



## P7 – Energy Response Characteristics of a RadFET Radiation Detector

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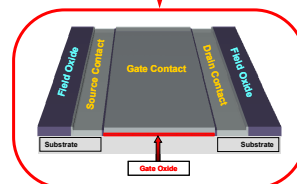
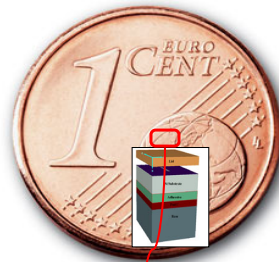
<sup>2</sup>Vienna University of Technology, Atomic Institute, 1020 Vienna, Austria

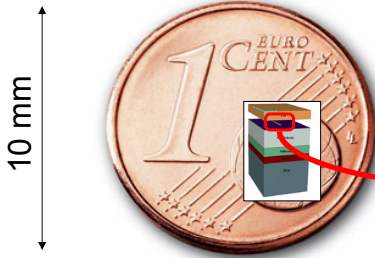
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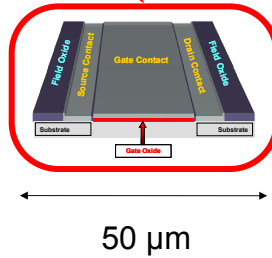
## Outline

- Solution to Problem P7
  - Geometry Modifications of the Problem
- Used are the Monte Carlo codes
  - FLUKA; full solution to the problem
  - Geant4; partial solution of the problem
- Uncertainty Budget

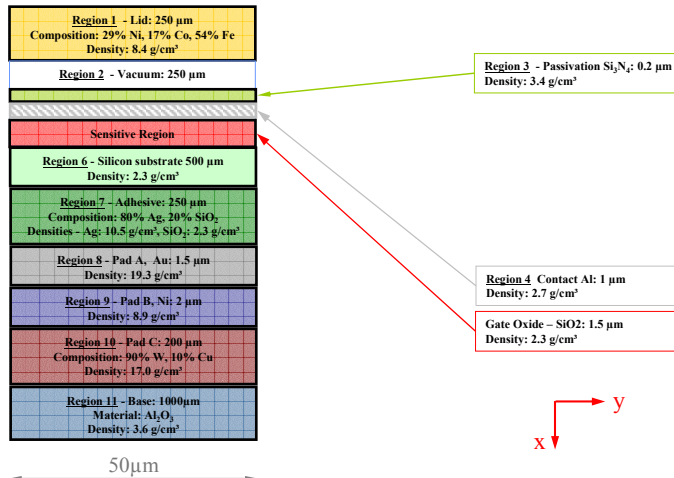




What sizes are we simulating?

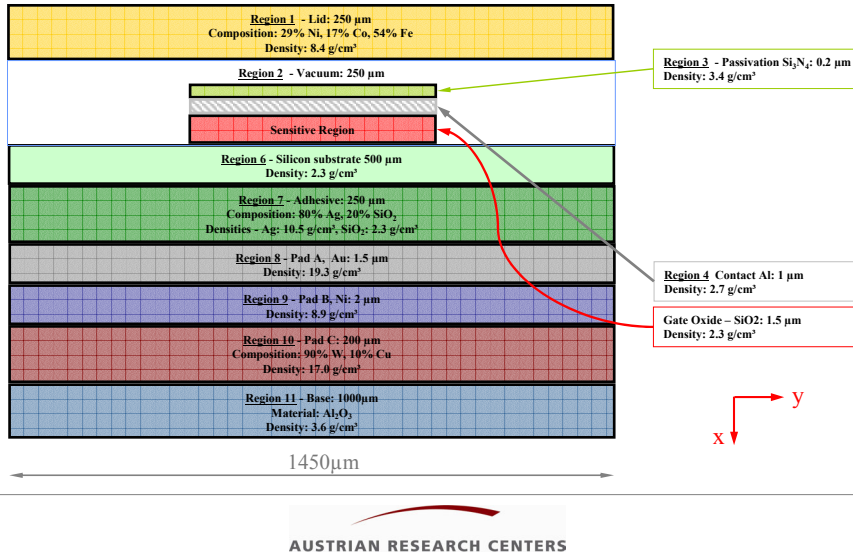


## The given Geometry and Modifications

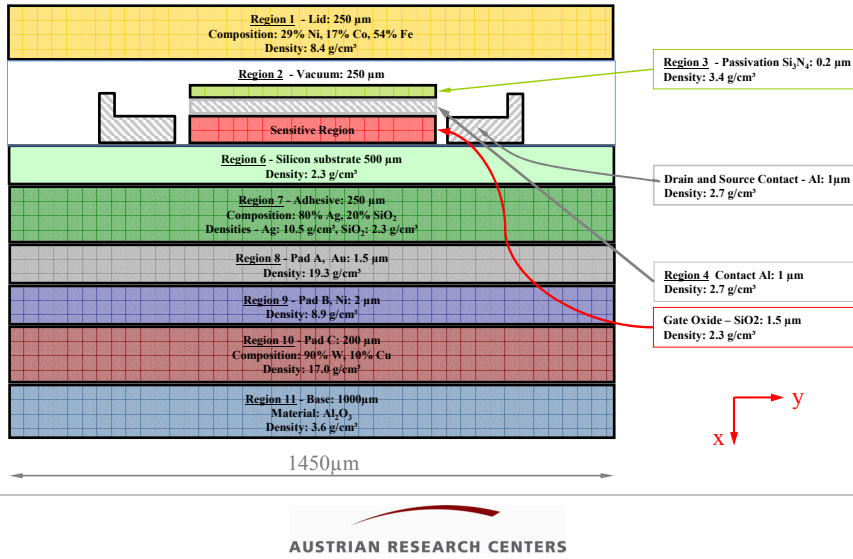




# The given Geometry and Modifications

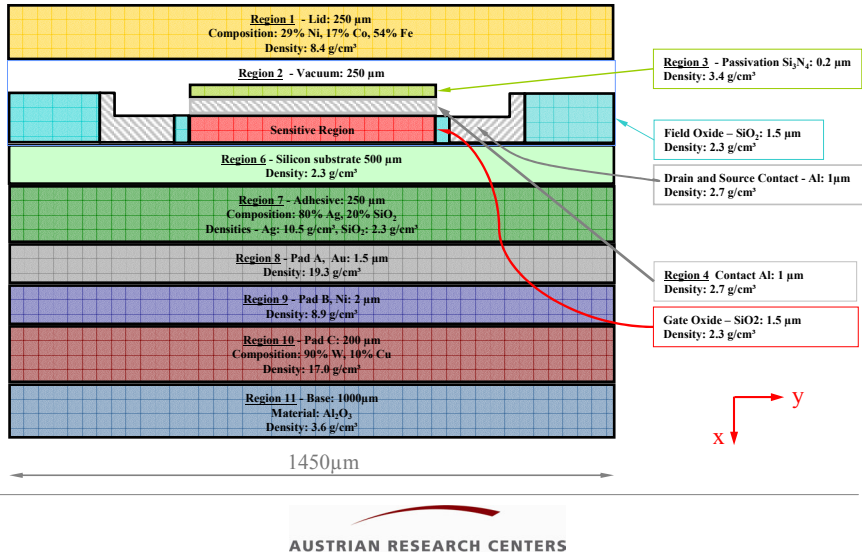


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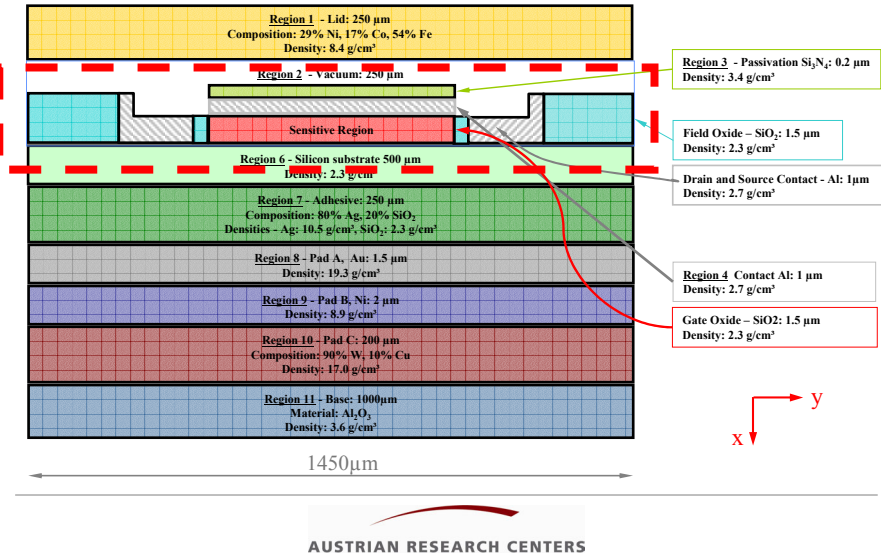




# The given Geometry and Modifications

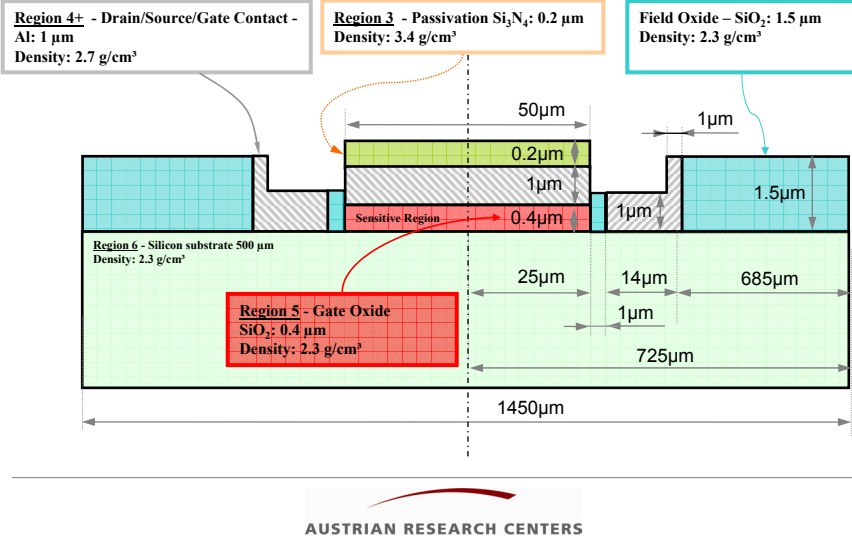


# The given Geometry and Modifications

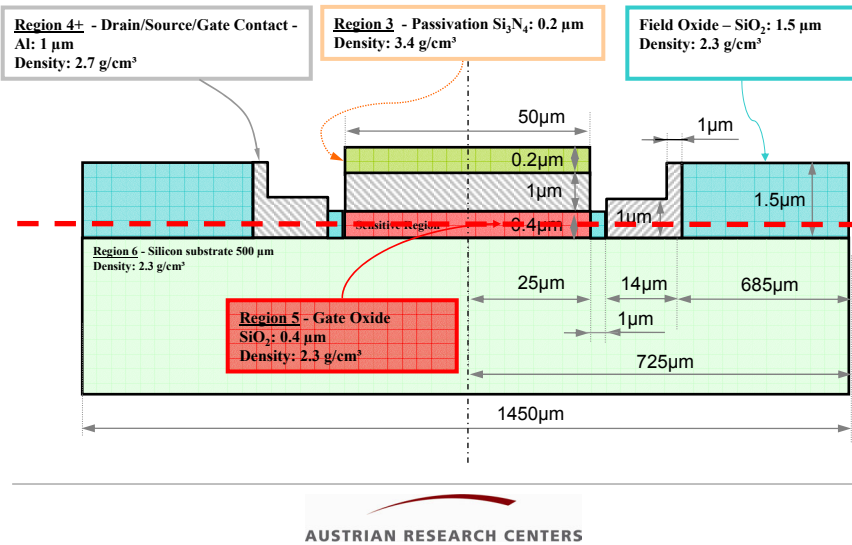




# The given Geometry and Modifications



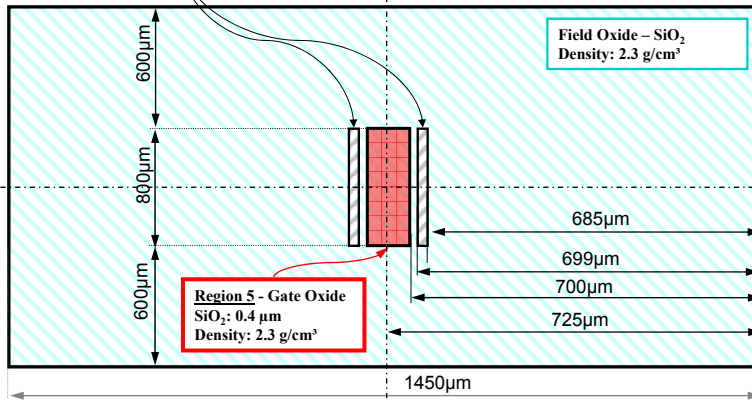
# The given Geometry and Modifications





**Region 4+** - Drain/Source Contact -  
Al: 1  $\mu\text{m}$   
Density: 2.7  $\text{g}/\text{cm}^3$

**Cross section:**  
Cut through: Gate Oxide / Field Oxide /  
Drain and Source Contact



## Monte Carlo Simulation with FLUKA & GEANT4

### MC Codes used

- FLUKA 2006 / Geant4.7.1
- Transport of
  - electromagnetic particles
  - hadronic particles
  - heavy ions
- Energy: 20 TeV to ...
  - 10keV (all particles)
  - thermal neutrons
  - 1 keV (ph, e<sup>-</sup>)
  - 250eV (ph, e<sup>-</sup>) / GEANT4 (LEEM)

### Hardware

- PC, Intel Pentium4, 2.4 GHz
- SGI/Altix, 64 bit Intel Itanium2, 1.4 GHz
- maximum number of starting photons:  $\text{NPS} = 10^9$
- stat. uncertainties:  $\sim < 3\%$
- average simulation time per setup:
  - 7 - 9 days



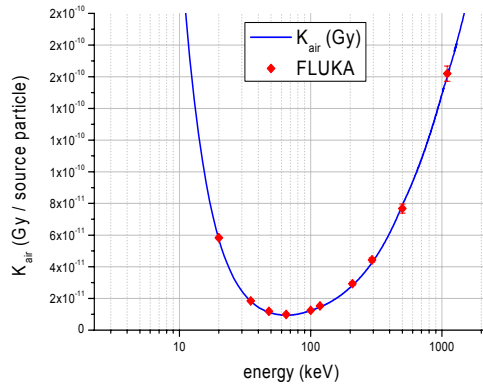
## Air Kerma calculation

- All materials are replaced by air
- Air Kerma can be calculated in two ways
  - using literature data
  - using FLUKA

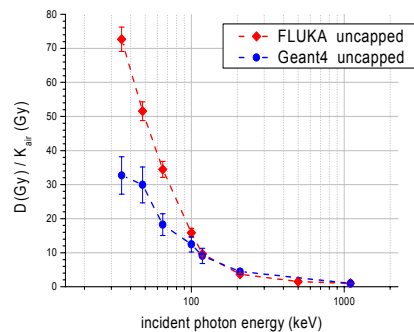
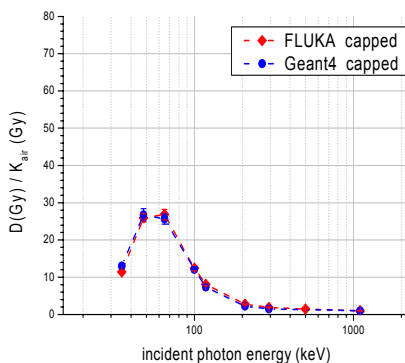
$$K_{air} = \int_0^{\infty} dE \cdot \Psi(E) \cdot \left(\frac{\mu_{en}}{\rho}\right)_{E,Z}$$

$$\Psi(E) = \Psi_{E_0} \delta(E - E_0)$$

$$K_{air} = \int_0^{\infty} dE \cdot \Psi_{E_0} \delta(E - E_0) \left(\frac{\mu_{en}}{\rho}\right)_{E,Z} = \Psi_{E_0} \left(\frac{\mu_{en}}{\rho}\right)_{E_0,Z}$$

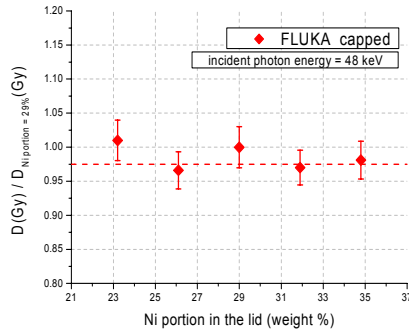
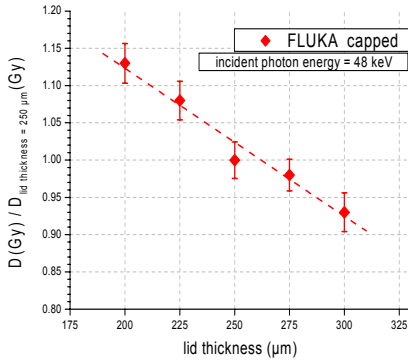


## Energy response function of the capped and uncapped RadFET

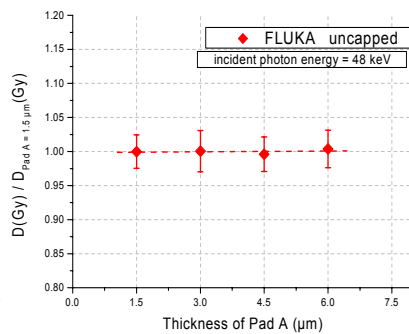
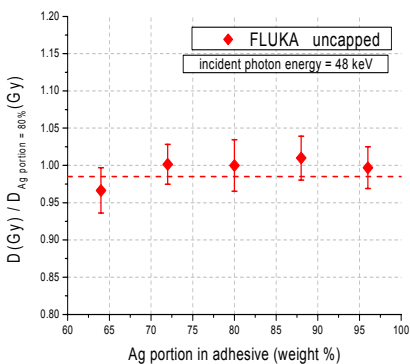




## Variation of Lid Thickness and Ni Portion

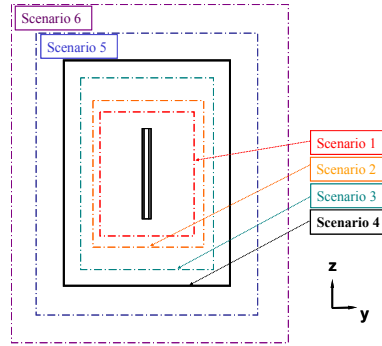
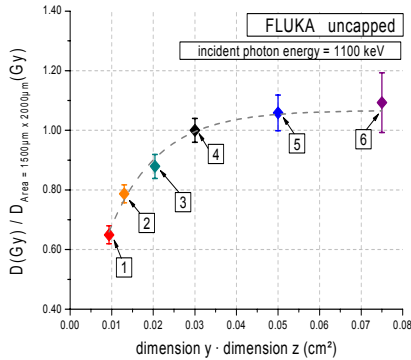


## Variation of Ag portion in the Adhesive and Underestimation of the thickness of Attach Pad A (uncapped device)





# Sensitivity of the solutions to the extent of the model in y- and z-directions



# Uncertainty Budget (FLUKA)

	capped		uncapped	
			$E_{ph} \geq 100 \text{ keV}$	$35 \text{ keV} \leq E_{ph} < 100 \text{ keV}$
Statistical uncertainty	5 %	5 %	5 %	5 %
Cross sections data	5 %	5 %	5 %	5 %
Model geometry	7 %	7 %	7 %	7 %
Mean code deviations	9 %	12 %	62 %	62 %
<b>Simulation uncertainty</b>	<b>13.5 %</b>	<b>15.6 %</b>	<b>63 %</b>	<b>63 %</b>
Lid thickness	13 %	--	--	--
Ni portion of the lid	3 %	--	--	--
Ag portion of adhesive	3 %	3 %	3 %	3 %
Thickness of attach pad A	3 %	3 %	3 %	3 %
<b>RadFET related uncertainty</b>	<b>14 %</b>	<b>4.5 %</b>	<b>4.5 %</b>	<b>4.5 %</b>
<b>Total simulation uncertainty</b>	<b>19.5 %</b>	<b>16.5 %</b>	<b>63.5 %</b>	<b>63.5 %</b>



## Conclusions

- The choice of the **geometry has considerable influence** on the result
- Response of “capped” and “uncapped” device differ most significantly incident for photon energies below 100 keV
- **Comparison of FLUKA and Geant4**
  - “capped” RadFET
    - good agreement
  - “uncapped” RadFET
    - incident photon energies  $\geq 100$  keV: reasonable agreement
    - incident photon energies  $< 100$  keV; significant disagreement
- **Variation of RadFET Parameters**
  - Increase of the lid thickness by 20% decreases the response in the gate oxide by 13%
  - No effect was found for the variation of
    - Lid composition
    - Composition of adhesive
    - Thickness of Pad A



Thanks for your Attention !!!



## Spatial Electron Fluence in capped RadFET due to 48keV incident photon irradiation

